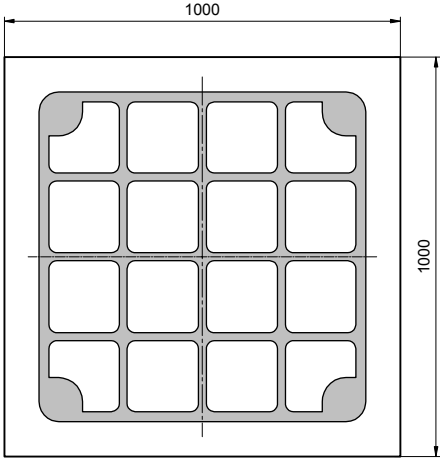


Radiation	Type	Technology	Electrodes
Red-orange	solderable	AllnGaP/GaAs	P (anode) up

 <p>PoC-05</p>	typ. dimensions ( $\mu\text{m}$ )
	<u>typ. thickness</u> 260 ( $\pm 20$ ) $\mu\text{m}$  <u>cathode</u> gold alloy, 1.5 $\mu\text{m}$  <u>anode</u> gold alloy, 1.5 $\mu\text{m}$

### Optical and Electrical Characteristics

$T_{\text{amb}} = 25^{\circ}\text{C}$ , unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100 \text{ mA}$	$V_F$		1.9	2.3	V
Forward voltage	$I_F = 300 \text{ mA}$	$V_F$		2.1		V
Reverse voltage	$I_F = 10 \mu\text{A}$	$V_R$	5			V
Radiant power <sup>1</sup>	$I_F = 100 \text{ mA}$	$\Phi_e$	4.6	6.0		mW
Radiant power <sup>1</sup>	$I_F = 300 \text{ mA}$	$\Phi_e$		16		mW
Luminous intensity <sup>1</sup>	$I_F = 100 \text{ mA}$	$I_V$	225	290		mcd
Peak wavelength	$I_F = 100 \text{ mA}$	$\lambda_p$	635	645	655	nm
Spectral bandwidth at 50%	$I_F = 100 \text{ mA}$	$\Delta\lambda_{0.5}$		16		nm
Switching time	$I_F = 100 \text{ mA}$	$t_r, t_f$		40		ns

<sup>1</sup>Measured on bare chip on TO-18 header with *EPIGAP* equipment

### Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-645-11-05				

**Packing:** Chips on adhesive film with wire-bond side on top